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(54) Title: DUAL AUXILIARY DOPANT INLETS ON EPI CHAMBER

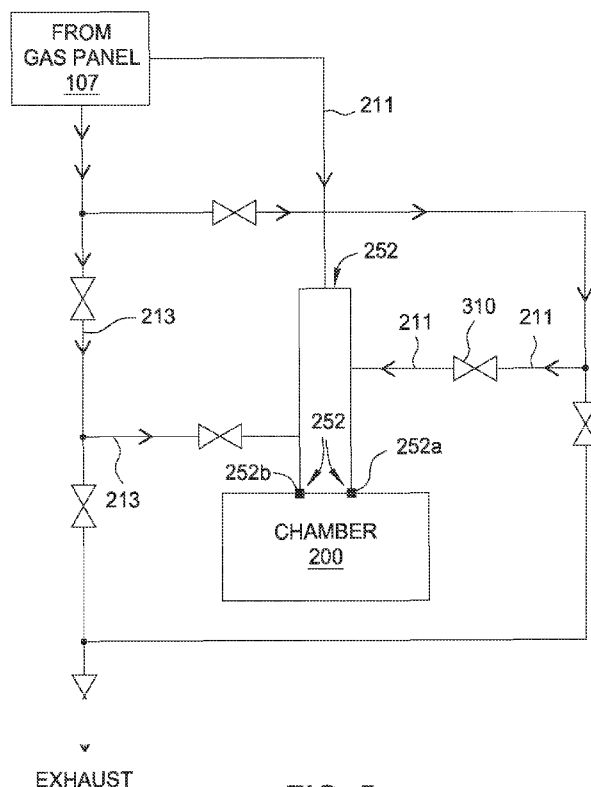


FIG. 5

(57) Abstract: The present invention provides methods and apparatus for processing semiconductor substrates with dual or multiple dopant inlets formed at different locations of an epitaxial chamber configured to supply dopant gases toward different locations of the substrate during deposition. In one embodiment, a gas delivery system configured to couple to an epitaxial deposition chamber includes a gas conduit has a first end and a second end configured to dispose in an epitaxial deposition chamber, the first end coupled to a gas panel and a second end branched out to include an auxiliary inner dopant inlet and an auxiliary outer dopant inlet, wherein the auxiliary inner dopant inlet and the auxiliary outer dopant inlet are independently controlled when implementing in the epitaxial deposition chamber.

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